

PNZ0334

PIN Photodiode

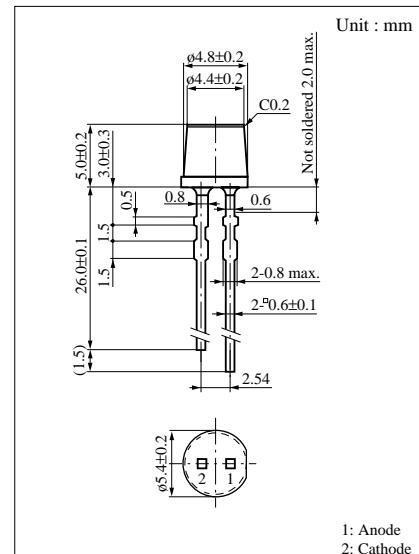
For optical fiber communication systems

■ Features

- Plastic type package (ϕ 5)
- High coupling capability suitable for plastic fiber
- High quantum efficiency
- High-speed response

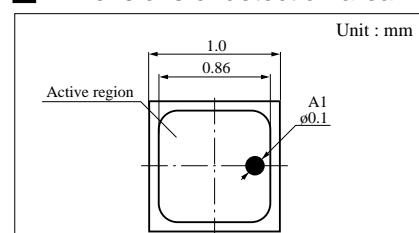
■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Reverse voltage (DC)	V _R	30	V
Power dissipation	P _D	100	mW
Operating ambient temperature	T _{opr}	-25 to +85	°C
Storage temperature	T _{stg}	-30 to +100	°C



1: Anode
2: Cathode

■ Dimensions of detection area



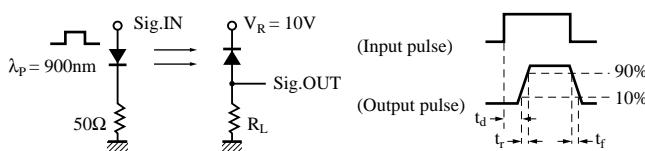
Unit : mm

■ Electro-Optical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Dark current	I _D	V _R = 10V		0.1	10	nA
Photo current	I _L	V _R = 10V, L = 1000 lx ^{*1}	5	7		µA
Peak sensitivity wavelength	λ _P	V _R = 10V		850		nm
Response time	t _r , t _f ^{*2}	V _R = 10V, R _L = 50Ω		2		ns
Capacitance between pins	C _t	V _R = 0V, f = 1MHz		6		pF
Acceptance half angle	θ	Measured from the optical axis to the half power point		70		deg.

^{*1} Measurements were made using a tungsten lamp (color temperature T = 2856K) as a light source.

^{*2} Switching time measurement circuit



t_d: Delay time

t_r: Rise time (Time required for the collector photo current to increase from 10% to 90% of its final value)

t_f: Fall time (Time required for the collector photo current to decrease from 90% to 10% of its initial value)

